

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of :

Hatakeyama et al.

Group Art Unit: TBA

Serial No.: TBA

Examiner: TBA

Filed: November 28, 2001

For: AMINE COMPOUNDS, RESIST COMPOSITIONS AND PATTERNING PROCESS

2/A  
D.G.  
1-17-02

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

Prior to initial examination, please amend the above-identified application as follows:

IN THE CLAIMS:

*Please amend the claims as follows:*

9. (Amended) A process for forming a resist pattern comprising the steps of:
- applying the resist composition of claim 5 onto a substrate to form a coating,
- heat treating the coating and then exposing it to high-energy radiation having a wavelength of less than 300 nm or electron beams through a photo mask, and
- optionally heat treating the exposed coating and developing it with a developer.

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